
2SA673, 2SA673A

Silicon PNP Epitaxial

HITACHI

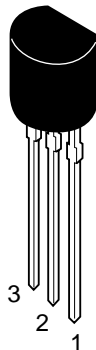
ADE-208-125 (Z)
1st. Edition
Mar. 2001

Application

- Low frequency amplifier
- Complementary pair with 2SC1213 and 2SC1213A

Outline

TO-92 (1)



1. Emitter
2. Collector
3. Base

2SA673, 2SA673A

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	2SA673	2SA673A	Unit
Collector to base voltage	V_{CBO}	-35	-50	V
Collector to emitter voltage	V_{CEO}	-35	-50	V
Emitter to base voltage	V_{EBO}	-4	-4	V
Collector current	I_C	-500	-500	mA
Collector power dissipation	P_C	400	400	mW
Junction temperature	T_j	150	150	°C
Storage temperature	T_{stg}	-55 to +150	-55 to +150	°C

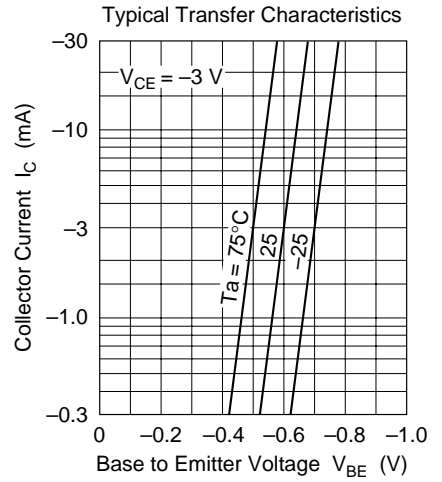
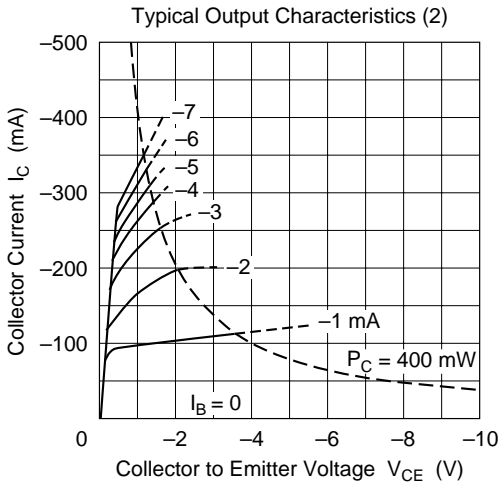
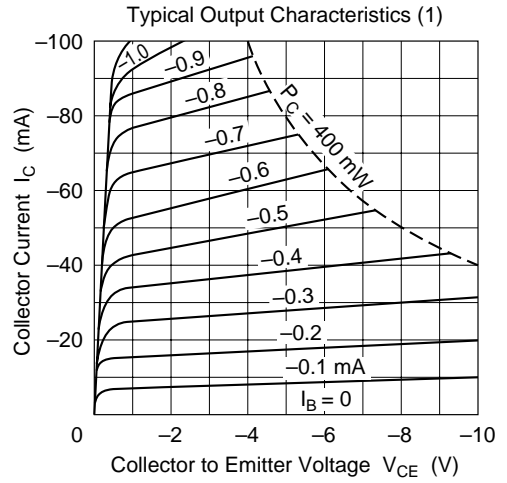
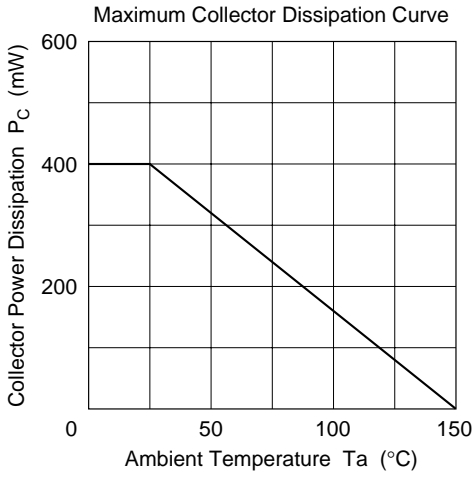
Electrical Characteristics (Ta = 25°C)

Item	Symbol	2SA673			2SA673A			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	-35	—	—	-50	—	—	V	$I_C = -10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-35	—	—	-50	—	—	V	$I_C = -1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-4	—	—	-4	—	—	V	$I_E = -10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-0.5	—	—	-0.5	μA	$V_{CB} = -20 \text{ V}, I_E = 0$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	-0.2	-0.6	—	-0.2	-0.6	V	$I_C = -150 \text{ mA}, I_B = -15 \text{ mA}^{*2}$
DC current transfer ratio	h_{FE}^{*1}	60	—	320	60	—	320		$V_{CE} = -3 \text{ V}, I_C = -10 \text{ mA}$
DC current transfer ratio	h_{FE}	10	—	—	10	—	—		$V_{CE} = -3 \text{ V}, I_C = -500 \text{ mA}^{*2}$
Base to emitter voltage	V_{BE}	—	-0.64	—	—	-0.64	—	V	$V_{CE} = -3 \text{ V}, I_C = -10 \text{ mA}$

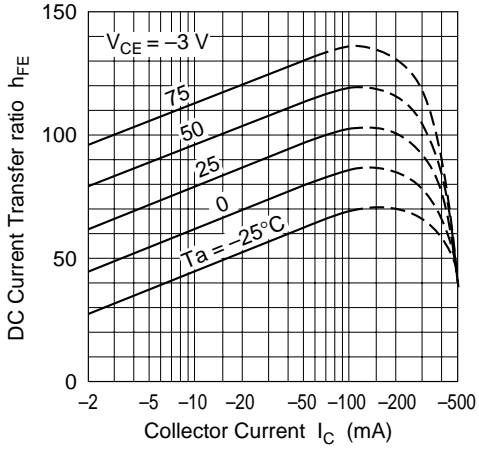
Notes: 1. The 2SA673 and 2SA673A are grouped by h_{FE} as follows.

2. Pulse test

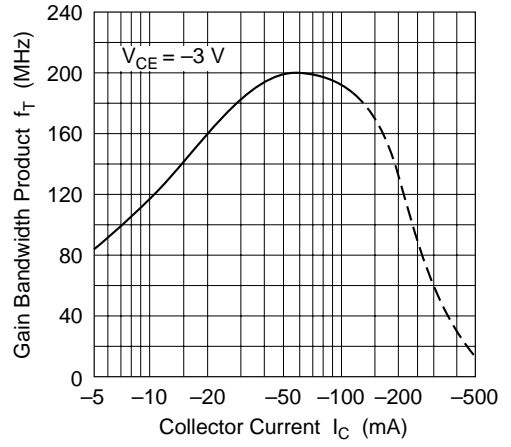
B	C	D
60 to 120	100 to 200	160 to 320



DC Current Transfer Ratio vs. Collector Current

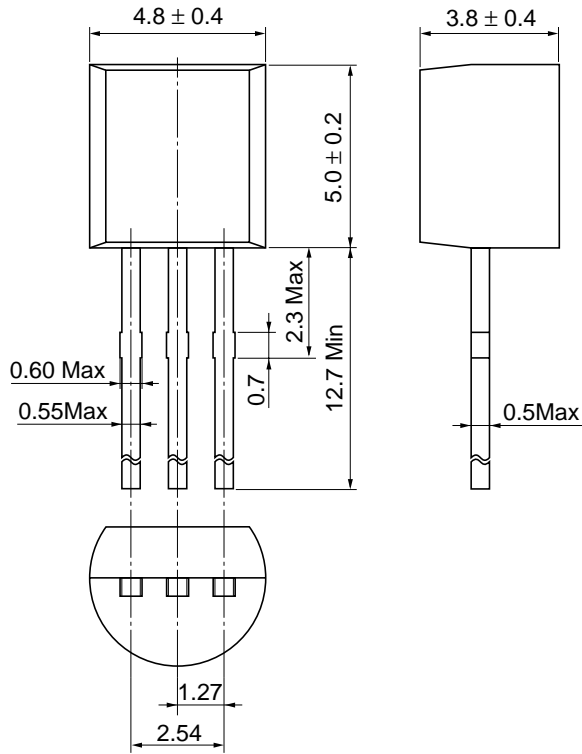


Gain Bandwidth Product vs. Collector Current



Package Dimensions

As of January, 2001
Unit: mm



Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	0.25 g

Cautions

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Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL NorthAmerica : <http://semiconductor.hitachi.com/>
Europe : <http://www.hitachi-eu.com/hel/ecg>
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic Components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 585160

Hitachi Asia Ltd.
Hitachi Tower
16 Collyer Quay #20-00,
Singapore 049318
Tel: <65>-538-6533/538-8577
Fax: <65>-538-6933/538-3877
URL: <http://www.hitachi.com.sg>

Hitachi Asia Ltd.
(Taipei Branch Office)
4/F, No. 167, Tun Hwa North Road,
Hung-Kuo Building,
Taipei (105), Taiwan
Tel: <886>-(2)-2718-3666
Fax: <886>-(2)-2718-8180
Telex: 23222 HAS-TP
URL: <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon,
Hong Kong
Tel: <852>-(2)-735-9218
Fax: <852>-(2)-730-0281
URL: <http://www.hitachi.com.hk>

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